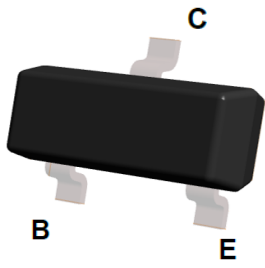
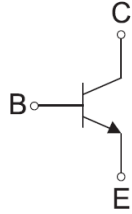
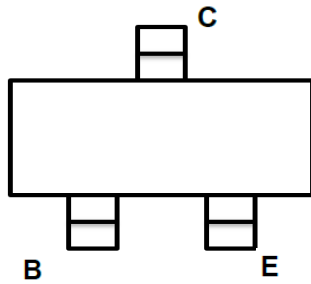


General Purpose Transistors NPN Silicon



Top View

SOT-23



Product Summary

- V_{CE0} 400V
- I_c 200mA
- P_c 350mW

FEATURE

- High Collector-Emitter Voltage
- Complement to MMBTA94

■ MAXIMUM RATINGS ($T_A=25^\circ\text{C}$ unless otherwise noted)

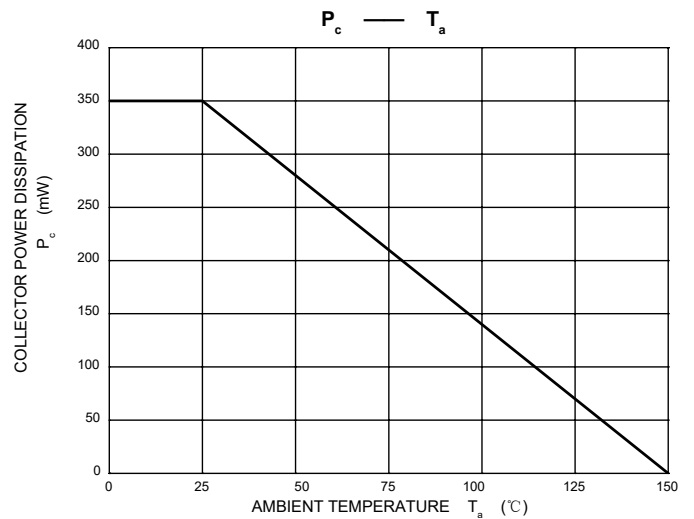
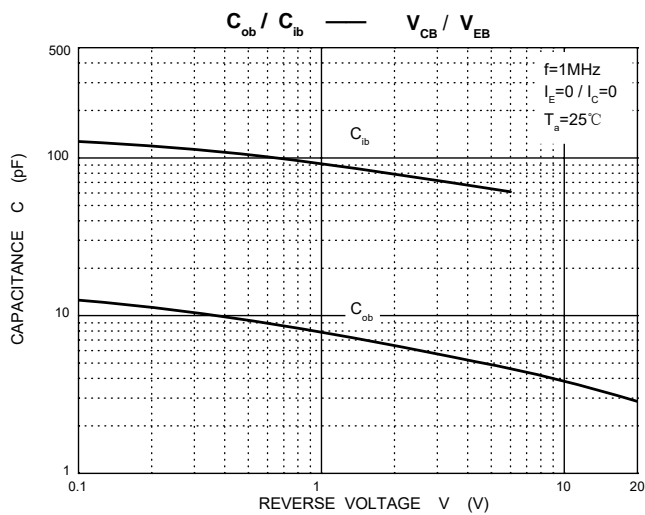
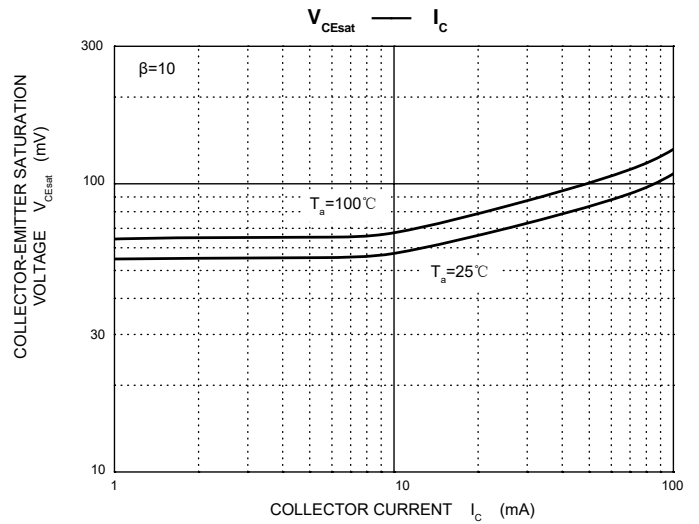
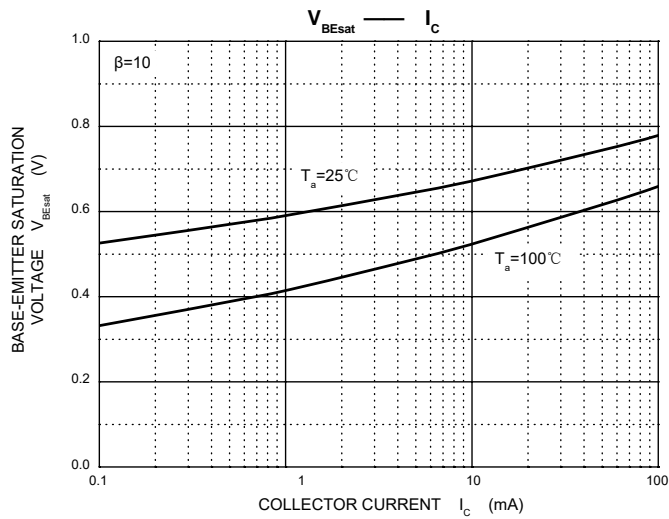
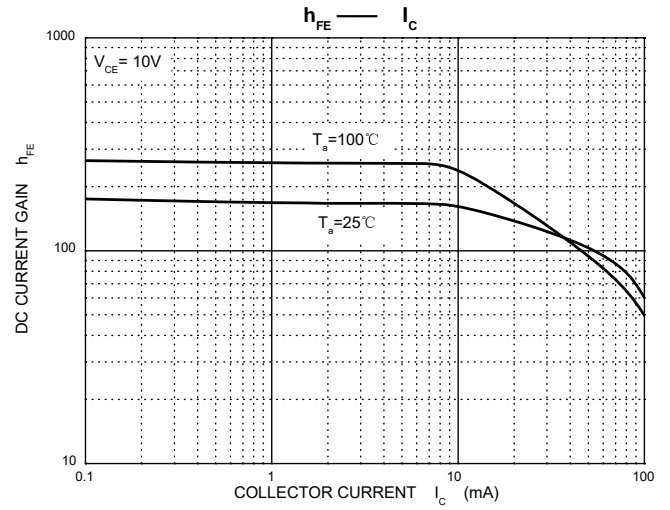
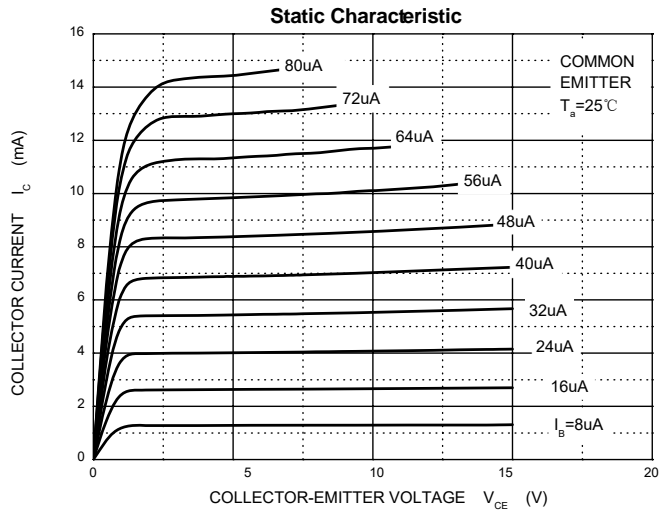
Parameter	Symbol	Limit	Unit
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CE0}	400	V
Emitter-Base Voltage	V_{EBO}	6	V
Collector Current -Continuous	I_c	0.2	A
Power Dissipation	P_c	0.35	W
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C/W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

■ **Electrical Characteristics** ($T_J=25^\circ\text{C}$ unless otherwise noted)

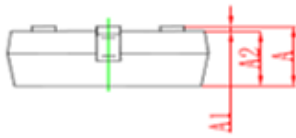
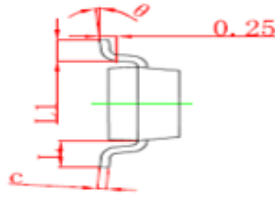
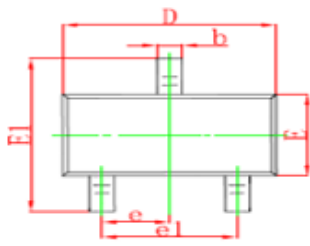
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}, I_E=0$	400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}^*$	$I_C=1\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}, I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=400\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=4\text{V}, I_C=0$			0.1	μA
DC current gain	$h_{FE(1)}^*$	$V_{CE}=10\text{V}, I_C=1\text{mA}$	40			
	$h_{FE(2)}^*$	$V_{CE}=10\text{V}, I_C=10\text{mA}$	50		200	
	$h_{FE(3)}^*$	$V_{CE}=10\text{V}, I_C=50\text{mA}$	45			
	$h_{FE(4)}^*$	$V_{CE}=10\text{V}, I_C=100\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(sat)1}^*$	$I_C=1\text{mA}, I_B=0.1\text{mA}$			0.4	V
	$V_{CE(sat)2}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.5	V
	$V_{CE(sat)3}^*$	$I_C=50\text{mA}, I_B=5\text{mA}$			0.75	V
Base-emitter saturation voltage	$V_{BE(sat)}^*$	$I_C=10\text{mA}, I_B=1\text{mA}$			0.75	V
Collector output capacitance	C_{ob}	$V_{CB}=20\text{V}, I_E=0, f=1\text{MHz}$			7	pF
Emitter input capacitance	C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1\text{MHz}$			130	pF
Transition frequency	f_T	$V_{CE}=20\text{V}, I_C=10\text{mA}, f=30\text{MHz}$	50			MHz

*Pulse test: pulse width $\leq 300\mu\text{s}$, duty cycle $\leq 2.0\%$.

■ Typical Performance Characteristics

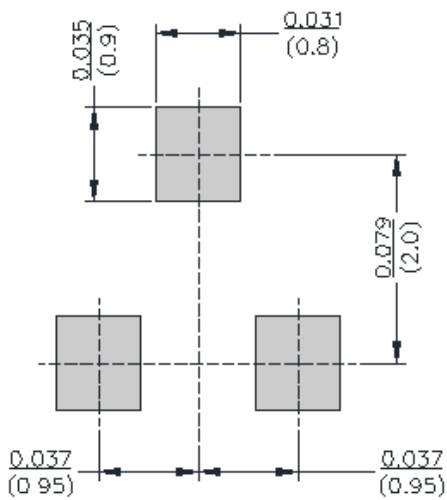


■ SOT-23 Package information



Symbol	Dimensions in Millimeter		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

■ SOT-23 Suggested Pad Layout



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